Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	533858	capacitor\$3 or capacitive	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 18:55
L2	127871	polysilicon or (polycrystalline adj (silicon or si)) or polysi or poly-si or poly-silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 18:55
L3	1319892	semiconduct\$3 or silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 18:56
L4	125860	(decoupl\$3 or coupl\$3) with 1	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 18:56
L5	4104590	well\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 18:57
L6	63158	3 same (implant\$3 or diffus\$5) same (dopant\$1 or impurit\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 18:59
L7	24271	mim or (metal-insulating-metal) or (metal-insulator-metal) or (metal adj insulat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM TDB	OR	ON	2005/03/20 19:00
L8	149389	tan or (tantalum adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:00
L9	11944	ta2o5 or ("ta.sub.2 o.sub.5") or (tantalum adj pentoxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:02

L10	4497	dielectric with 9	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:02
L11	4130009	5 or 6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:03
L12	2241	1 and 2 and 11 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:03
L13	349	12 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:03
L14	129	8 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:04
L19	220	13 not 14	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/20 19:33